

occasion, tensile stress is generated in the GaN semiconductor layer, so that there is a risk of occurrence of cracking as a result. Even in the case where cracking does not occur, distortion occurs in the lattice. Hence, the GaN semiconductor device cannot fulfill its original function.

AS
End

IN THE CLAIMS:

✓ Please cancel claims 7, 12-19, 21 and 22 without prejudice or disclaimer.

10020460 121801